

### **IRFS4321TRRPBF**

#### **IRFS4321TRRPBF Information**



For Reference Only

**Part Number** IRFS4321TRRPBF **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 150V 83A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# **IRFS4321TRRPBF Specifications**

Manufacturer Part Number       IRFS4321TRRPBF         Manufacturer       Infineon Technologies         Category       Discrete Semiconductor Products         Transistors - FETs, MOSFETs - Single         Package       TO-263-3, D2Pak (2 Leads + Tab), TO-263AB         Series       HEXFET?         FET Type       N-Channel         Technology       MOSFET (Metal Oxide)         Drain to Source Voltage (Vdss)       150V         Current - Continuous Drain (Id) @ 25°C       85A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       110nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       4460pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       350W (Tc)         Rds On (Max) @ Id, Vgs       15 mOhm @ 33A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       D2PAK         Package (Constant)       TO 263 3 D3Pak (2 Loads + Tab), TO 263 AB		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4460pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)350W (Tc)Rds On (Max) @ Id, Vgs15 mOhm @ 33A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK	Manufacturer Part Number	IRFS4321TRRPBF
Package         TO-263-3, D2Pak (2 Leads + Tab), TO-263AB           Series         HEXFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         150V           Current - Continuous Drain (Id) @ 25°C         85A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4460pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         350W (Tc)           Rds On (Max) @ Id, Vgs         15 mOhm @ 33A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         D2PAK	Manufacturer	Infineon Technologies
Package Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 85A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 15 mOhm @ 33A, 10V Operating Temperature Supplier Device Package D2PAK	Category	Discrete Semiconductor Products
SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4460pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)350W (Tc)Rds On (Max) @ Id, Vgs15 mOhm @ 33A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK		Transistors - FETs, MOSFETs - Single
FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  150V  Current - Continuous Drain (Id) @ 25°C  85A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sty @ 250μA  Gate Charge (Qg) (Max) @ Vgs  110nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  4460pF @ 25V  Vgs (Max)  ±20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  15 mOhm @ 33A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4460pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)350W (Tc)Rds On (Max) @ Id, Vgs15 mOhm @ 33A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK	Series	HEXFET?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  85A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  15 mOhm @ 33A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4460pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)350W (Tc)Rds On (Max) @ Id, Vgs15 mOhm @ 33A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK	Technology	MOSFET (Metal Oxide)
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Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  4460pF @ 25V  Vgs (Max)  ±20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  15 mOhm @ 33A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  15 mOhm @ 33A, 10V  Operating Temperature  Operating Type  Surface Mount  Supplier Device Package  4460pF @ 25V  44	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)350W (Tc)Rds On (Max) @ Id, Vgs15 mOhm @ 33A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK	Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
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Rds On (Max) @ Id, Vgs15 mOhm @ 33A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Surface Mount  Supplier Device Package D2PAK	Power Dissipation (Max)	350W (Tc)
Mounting Type Surface Mount Supplier Device Package D2PAK	Rds On (Max) @ Id, Vgs	15 mOhm @ 33A, 10V
Supplier Device Package D2PAK	Operating Temperature	-55°C ~ 175°C (TJ)
**	Mounting Type	Surface Mount
Pockago / Coso	Supplier Device Package	D2PAK
10-203-3, D2Fak (2 Leaus + 1au), 10-203Ab	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Report errors?		Report errors?

#### **IRFS4321TRRPBF** Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **IRFS4321TRRPBF Payment Methods**





















# **IRFS4321TRRPBF Shipping Methods**













If you have any question about IRFS4321TRRPBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com